DOCUMENT CHANGE REQUEST

DCR number 1005

Changes required for: General

Originator: Steve Jeffery

Date: 2016/12/14

Date sent: 2016/06/16

Organisation: ESCC Executive

Status: IMPLEMENTED

Title:	Transistors Low Power PNP, based on type 2N5401		
Number:	5202/014	Issue:	6

Other documents affected:

Page:

12

Paragraph:

2.4.1

Original wording:

Collector-Base Breakdown Voltage Test Condition: IC = -100mA;

Emitter-Base Breakdown Voltage Test Condition: IC = -10mA

Proposed wording:

Collector-Base Breakdown Voltage Test Condition: IC = -100uA;

Emitter-Base Breakdown Voltage Test Condition: IC = -10uA

[Note - there are also some additional minor editorial and formatting changes]

See attachment (MSWord 2010 file) 5202/014 Issue 7 Draft A.

Justification:

As identifed by STMicroelectronics, notified by Aïssa NEHDI: These IC test conditions were changed (typographical errors) during the last update of the spec.

Some additional editorial and formatting errors were found during the subsequent review of 5202/014 Issue 4 which was made when raising this DCR on behalf of STMicroelectronics.

Attachments:
5202014_draft_7a.docx
Modifications:
N/A
Approval signature:
Date signed:
2016-12-14